IN THE CLAIMS

Please amend claim 31.

Please cancel claims 40-43 and 45-54 without prejudice.

Please enter the pending claims, including claims 31-39, as follows:

31. (Currently Amended) A method comprising:

providing a substrate;

forming a metal layer over said substrate, said metal layer comprising a bond pad and a first member, said bond pad and said first member being separated by a gap;

forming a first material over said bond pad and over said first member, said first material having a low dielectric constant, said first material having at least a minimum thickness that is sufficient to completely fill said gap, said first material doped with fluorine atoms;

forming a second material over said first material, said second material being thin and resistant to moisture penetration, said second material being kept out of said gap;

forming an opening through said second material and said first material to expose a top surface of said bond pad, said opening having sidewalls comprising edges of said second material and said first material;

forming a third material over said second material, said sidewalls of said opening, and said top surface of said bond pad, said third material being conductive, said third material having a thickness sufficient to prevent moisture penetration; and

forming a contact over said opening.

32. (Unchanged) The method of claim 31 wherein said gap has a high aspect ratio.

33. (Unchanged) The method of claim 32 wherein said high aspect ratio is around 2.0.

34. (Unchanged) The method of claim 31 wherein said first material has a dielectric constant of less than 4.0.

35. (Unchanged) The method of claim 31 wherein said first material is silicon dioxide.

36. (Unchanged) The method of claim 31 wherein said first material is doped with fluorine atoms to reduce dielectric constant.

37. (Unchanged) The method of claim 31 wherein said second material is hermetic.

38. (Unchanged) The method of claim 31 wherein said second material is silicon nitride.

39. (Unchanged) The method of claim 38 wherein said silicon nitride has a thickness of between 500 – 1,500 Angstroms.

40.-54. (Canceled)